

**16th International Conference on Mid-IR Optoelectronics:  
Materials and Devices MIOMD-XIV (MIOMD 2023)  
MIOMD1: Materials Development, Growth, and  
Characterization for Infrared Optoelectronics**

**Mirchandani<sup>1</sup>**

<sup>1</sup> *Syrnatec Photovoltaic Inc., 95 Pond PL, Middletown, Connecticut 06457-8736, United States*

Halide perovskites have recently attracted significant attention as a promising material for optoelectronic applications due to their high absorption coefficient, long carrier lifetime, and low-cost processing. In particular, CsPbBr<sub>3</sub> perovskite has emerged as a promising candidate for infrared optoelectronic applications because of its narrow bandgap and high quantum efficiency. However, the synthesis and growth of high-quality CsPbBr<sub>3</sub> perovskites with controlled morphology and crystal structure remains a challenge.

Syrnatec has developed innovative technology for the growth, characterization, and development of halide perovskites. The technology is based on a two-step solution process, which involves the deposition of a precursor film followed by annealing to form the perovskite.

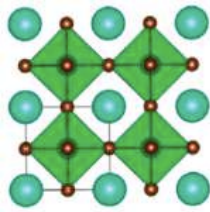
The precursor film was deposited using a novel spin-coating method that utilizes a mixture of PbBr<sub>2</sub> and CsBr in dimethyl sulfoxide (DMSO). The deposition was followed by annealing at a temperature of 150°C for 15 minutes to convert the precursor film to the perovskite.

The synthesized CsPbBr<sub>3</sub> perovskite was characterized using various techniques such as X-ray diffraction, scanning electron microscopy, and photoluminescence spectroscopy. The X-ray diffraction patterns of the perovskite showed sharp diffraction peaks, indicating excellent crystallinity. The scanning electron microscopy images revealed that the perovskite had a well-defined morphology with a cubic shape. The photoluminescence spectra of the perovskite showed a narrow emission peak at around 510 nm, indicating a narrow bandgap of 2.25 eV and indicative of high quantum efficiency.

The unique technology also enables the control of the crystal structure and morphology of the synthesized CsPbBr<sub>3</sub> perovskite. By adjusting the annealing temperature and time, we were able to obtain different crystal structures of the perovskite, including tetragonal and orthorhombic structures. We were also able to control the morphology of the perovskite by varying the concentration of the precursor solution.

Our experiments demonstrated that the synthesized CsPbBr<sub>3</sub> perovskite has potential applications in United States optoelectronics. The photodetector showed excellent photoresponse with 23.4% external quantum efficiency and a fast response time of 40ms.

Finally, this proposed technology will be having a potential for the large-scale production of CsPbBr<sub>3</sub> perovskite for US infrared optoelectronic applications like solar cells, photodetectors, and light-emitting diodes. The technology will provide a simple and low-cost solution-based approach for the synthesis and growth of high-quality CsPbBr<sub>3</sub> perovskite with controlled crystal structure and morphology. The potential of the technology for large-scale production of CsPbBr<sub>3</sub> perovskite which makes it a promising candidate for the commercialization of infrared optoelectronics applications in US.



Cubic CsPbBr<sub>3</sub>  
Figure 1:  
Structure of  
CsPbBr<sub>3</sub>

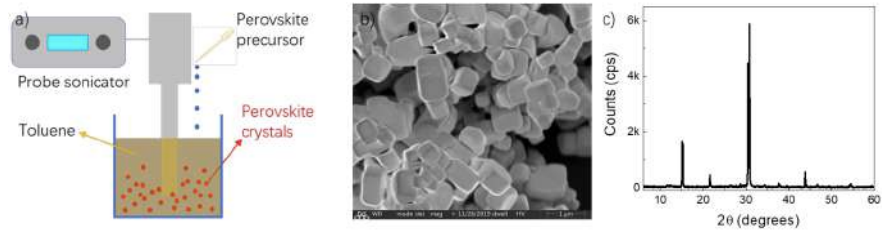


Figure 2: a. Proposed experimental set up for perovskite crystal synthesis, b. SEM image of synthesized CsPbBr<sub>3</sub>, c. XRD characterization of crystal

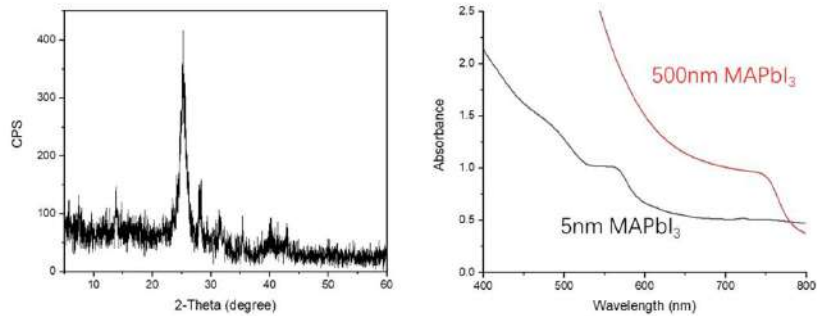


Figure 3: The XRD results. Absorbance spectra shows a significant blue shift from near IR absorption edge (750nm-800nm) to orange-red light wavelength (560nm-600nm), indicating the small size crystals exhibited the “quantum confinement,” which occurs usually when crystal size goes below 5nm.

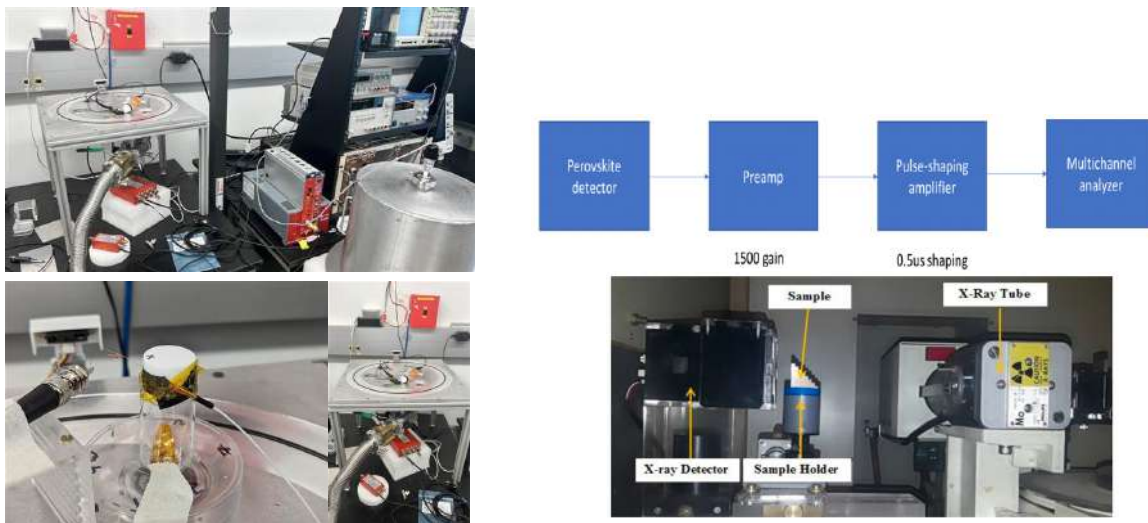


Figure 4: Proposed experimental set up

X-ray Tube Voltage (kV)	Max. Energy	X-ray X-ray Tube Current (μA)
10	10 keV	10, 20, 40, 60, 80, 100, 120, 140, 160, 180, 200
20	20 keV	10, 20, 40, 60, 80, 100, 120, 140, 160, 180, 198
30	30 keV	10, 20, 40, 60, 80, 100, 110, 120, 132
40	40 keV	10, 20, 30, 40, 50, 60, 70, 80, 90, 99
50	50 keV	5, 10, 20, 30, 40, 50, 60, 70, 79

THE 16TH INTERNATIONAL CONFERENCE ON

# Mid-IR Optoelectronics: Materials and Devices

AUGUST 6 - 10, 2023 • NORMAN, OKLAHOMA USA

## MIOMD - XVI

## MIOMD 2023 Copyright Agreement

**Presenter's Name** Yash Mirchandani

**Authors(s)** Yash Mirchandani

**Presentation Title:** MIOMD1: Materials Development, Growth, and Characterization for Infrared Optoelectronics

---

Note: this Copyright License remains binding regardless of revisions to presentation title, scheduling information, names of authors and/or presenters.

MIOMD 2023 is advising that all electronic recorded formats and electronic copies of all accepted presentations/ abstracts (including any oral component and questions and answers during any sessions) may be made available during and following the event as described below. By submitting your abstract and agreeing to participate in the meeting, it is understood that you agree to the following:

- I have read and agree to the following copyright terms and understand it is my responsibility as the submitting author to get all approvals with other authors and organization(s) prior to presenting.
- I consent to MIOMD 2023, through their designated vendor(s), audio and/or videotaping my presentation (including questions and answers) of my presentation during the MIOMD 2023 meeting.
- The videotape and audiotape from my presentation may be reproduced in whole or in part by MIOMD 2023, and in any and all forms as may be chosen by MIOMD 2023 including, but not limited to, making my presentation available to MIOMD 2023 meeting attendees and AVS members.
- MIOMD 2023 shall also have the right to use my name, abstract, recorded voice, photograph, biography, video, session recording, and other materials for the purpose of promoting my session(s) and MIOMD 2023.
- I have no right of approval, no claim for compensation, no right to a copy of the recording of my presentation, and no claim (including without limitation, claims based upon invasion of privacy, defamation, or right of publicity) arising out of or in connection with, any use, alteration, or use of my presentation in composite form.
- Notwithstanding the above, I retain all copyrights and intellectual property rights to all materials provided or presented by me. On behalf of myself and any co-authors, I certify that I have ownership rights to my presentation and supporting materials and that I am responsible and have obtained appropriate releases for any previously copyrighted material included in the presentation.
- I provide MIOMD 2023 with a perpetual, royalty-free, nonexclusive copyright license to post all electronic recorded formats and electronic copies of my presentation/abstract to the MIOMD 2023 Website/Mobile app/Online Scheduler and AVS Technical Library and for any other use by MIOMD 2023.
- On behalf of myself and any co-authors, I shall indemnify, defend and hold harmless MIOMD 2023/AVS, its officers, directors, employees, agents, and each of them, from any claim, demand, loss, liability, damage or expense arising in any way from the presentation and/or supporting materials. The terms of this provision shall survive the termination or expiration of this Agreement.